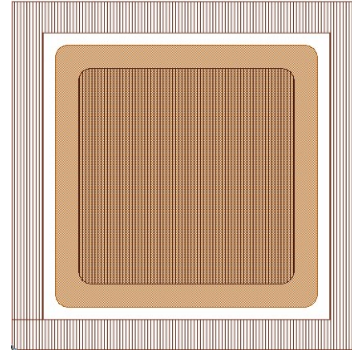


Features

- 3.3V uni-directional ESD diode
- Ultra low leakage: nA level
- Typical peak pulse power: 80W (8/20μs)
- Ultra low clamping voltage
- Standoff voltages: 3.3V
- Complies with IEC 61000-4-2 standards:
 - Air discharge: ±30kV
 - Contact discharge: ±30kV

Die Appearance



Circuit Diagram



Wafer Information

Item	Description
Wafer Size	6 inch (150um)
Wafer Thickness	100um ± 10um
Die Size (including scribe lane)	185um x 185um
Bond Pad Opening	72umx 72um
Scribe Lane Width	60um
Gross Die Per Wafer	438,000
Yield	96%
Top Metal (for wire bond)	3μm AlSiCu
Backside Metal (for die bond)	TiNiAg

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	80	W
Peak Pulse Current (8/20 μs)	I _{PP}	10	A
Operating Temperature Range	T _J	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T _{stg}	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			3.3	V	
Punch-Through Voltage	V _{PT}	3.5			V	I _{PT} = 2 μA
Snap-Back Voltage	V _{SB}		1		V	I _{SB} = 50mA
Reverse Leakage Current	I _R			100	nA	V _{RWM} = 3.3V
Clamping Voltage	V _C			12	V	I _{PP} = 1A (8 x 20 μs pulse)
Clamping Voltage	V _C			8	V	I _{PP} = 10A (8 x 20 μs pulse)
Junction Capacitance	C _J		0.6		pF	V _R = 0V, f = 1MHz

Note: Electrical parameters are only for die, performance may alter after assembly.

NOTICE

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